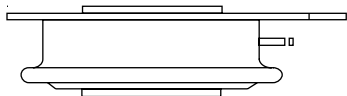


Phase Control Thyristors (Hockey PUK Version), 410 A



TO-200AB (A-PUK)

FEATURES

- Center amplifying gate
- Metal case with ceramic insulator
- International standard case TO-200AB (A-PUK)
- Lead (Pb)-free
- Designed and qualified for industrial level


RoHS
COMPLIANT

PRODUCT SUMMARY

$I_{T(AV)}$	410 A
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TYPICAL APPLICATIONS

- DC motor controls
- Controlled DC power supplies
- AC controllers

MAJOR RATINGS AND CHARACTERISTICS

PARAMETER	TEST CONDITIONS	VALUES	UNITS
$I_{T(AV)}$		410	A
	T_{hs}	55	°C
$I_{T(RMS)}$		780	A
	T_{hs}	25	°C
I_{TSM}	50 Hz	5700	A
	60 Hz	5970	
I^2t	50 Hz	163	kA ² s
	60 Hz	149	
V_{DRM}/V_{RRM}		400 to 2000	V
t_q	Typical	100	μs
T_J		- 40 to 125	°C

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS

TYPE NUMBER	VOLTAGE CODE	V_{DRM}/V_{RRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V_{RSM} , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	I_{DRM}/I_{RRM} MAXIMUM AT $T_J = T_J$ MAXIMUM mA
ST230C...C	04	400	500	30
	08	800	900	
	12	1200	1300	
	14	1400	1500	
	16	1600	1700	
	18	1800	1900	
	20	2000	2100	

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS			VALUES	UNITS
Maximum average on-state current at heatsink temperature	I _{T(AV)}	180° conduction, half sine wave double side (single side) cooled			410 (165)	A
					55 (85)	°C
Maximum RMS on-state current	I _{T(RMS)}	DC at 25 °C heatsink temperature double side cooled			780	A
Maximum peak, one-cycle non-repetitive surge current	I _{TSM}	t = 10 ms	No voltage reapplied	Sinusoidal half wave, initial T _J = T _J maximum	5700	
		t = 8.3 ms			5970	
		t = 10 ms	100 % V _{RRM} reapplied		4800	
		t = 8.3 ms			5000	
Maximum I ² t for fusing	I ² t	t = 10 ms	No voltage reapplied		163	kA ² s
		t = 8.3 ms			148	
		t = 10 ms	100 % V _{RRM} reapplied		115	
		t = 8.3 ms			105	
Maximum I ² √t for fusing	I ² √t	t = 0.1 to 10 ms, no voltage reapplied			1630	kA ² /s
Low level value of threshold voltage	V _{T(TO)1}	(16.7 % × π × I _{T(AV)}) < I < π × I _{T(AV)} , T _J = T _J maximum			0.92	V
High level value of threshold voltage	V _{T(TO)2}	(I > π × I _{T(AV)}), T _J = T _J maximum			0.98	
Low level value of on-state slope resistance	r _{t1}	(16.7 % × π × I _{T(AV)}) < I < π × I _{T(AV)} , T _J = T _J maximum			0.88	mΩ
High level value of on-state slope resistance	r _{t2}	(I > π × I _{T(AV)}), T _J = T _J maximum			0.81	
Maximum on-state voltage	V _{TM}	I _{pk} = 880 A, T _J = T _J maximum, t _p = 10 ms sine pulse			1.69	V
Maximum holding current	I _H	T _J = 25 °C, anode supply 12 V resistive load			600	mA
Maximum (typical) latching current	I _L				1000 (300)	

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum non-repetitive rate of rise of turned-on current	di/dt	Gate drive 20 V, 20 Ω, $t_r \leq 1$ μs $T_J = T_J$ maximum, anode voltage ≤ 80 % V_{DRM}	1000	A/μs
Typical delay time	t_d	Gate current 1 A, $di_g/dt = 1$ A/μs $V_d = 0.67$ % V_{DRM} , $T_J = 25$ °C	1.0	μs
Typical turn-off time	t_q	$I_{TM} = 300$ A, $T_J = T_J$ maximum, $di/dt = 20$ A/μs, $V_R = 50$ V, $dV/dt = 20$ V/μs, gate 0 V 100 Ω, $t_p = 500$ μs	100	

BLOCKING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum critical rate of rise of off-state voltage	dV/dt	$T_J = T_J$ maximum linear to 80 % rated V_{DRM}	500	V/μs
Maximum peak reverse and off-state leakage current	I_{RRM} , I_{DRM}	$T_J = T_J$ maximum, rated V_{DRM}/V_{RRM} applied	30	mA



TRIGGERING						
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES		UNITS
				TYP.	MAX.	
Maximum peak gate power	P _{GM}	T _J = T _J maximum, t _p ≤ 5 ms		10.0		W
Maximum average gate power	P _{G(AV)}	T _J = T _J maximum, f = 50 Hz, d% = 50		2.0		
Maximum peak positive gate current	I _{GM}	T _J = T _J maximum, t _p ≤ 5 ms		3.0		A
Maximum peak positive gate voltage	+ V _{GM}	T _J = T _J maximum, t _p ≤ 5 ms		20		V
Maximum peak negative gate voltage	- V _{GM}			5.0		
DC gate current required to trigger	I _{GT}	T _J = - 40 °C	Maximum required gate trigger/ current/voltage are the lowest value which will trigger all units 12 V anode to cathode applied	180	-	mA
		T _J = 25 °C		90	150	
		T _J = 125 °C		40	-	
DC gate voltage required to trigger	V _{GT}	T _J = - 40 °C		2.9	-	V
		T _J = 25 °C		1.8	3.0	
		T _J = 125 °C		1.2	-	
DC gate current not to trigger	I _{GD}	T _J = T _J maximum	Maximum gate current/voltage not to trigger is the maximum value which will not trigger any unit with rated V _{DRM} anode to cathode applied	10		mA
DC gate voltage not to trigger	V _{GD}			0.25		V

THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum operating temperature range	T_J			- 40 to 125	°C
Maximum storage temperature range	T_{Stg}			- 40 to 150	
Maximum thermal resistance, junction to heatsink	R_{thJ-hs}	DC operation single side cooled		0.17	K/W
		DC operation double side cooled		0.08	
Maximum thermal resistance, case to heatsink	R_{thC-hs}	DC operation single side cooled		0.033	
		DC operation double side cooled		0.017	
Mounting force, ± 10 %				4900 (500)	N (kg)
Approximate weight				50	g
Case style		See dimensions - link at the end of datasheet		TO-200AB (A-PUK)	

ΔR_{thJC} CONDUCTION						
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION		RECTANGULAR CONDUCTION		TEST CONDITIONS	UNITS
	SINGLE SIDE	DOUBLE SIDE	SINGLE SIDE	DOUBLE SIDE		
180°	0.015	0.017	0.011	0.011	T _J = T _J maximum	K/W
120°	0.018	0.019	0.019	0.019		
90°	0.024	0.024	0.026	0.026		
60°	0.035	0.035	0.036	0.036		
30°	0.060	0.060	0.060	0.061		

Note

- The table above shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC

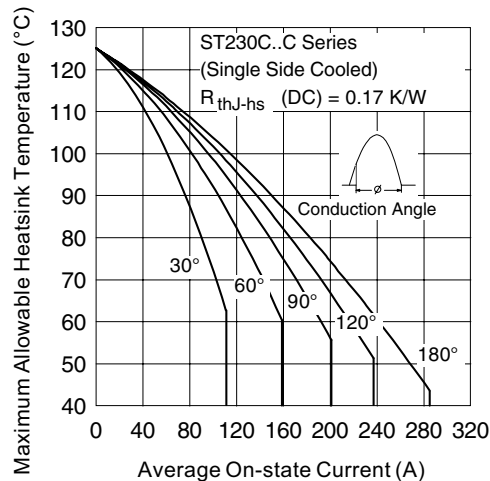


Fig. 1 - Current Ratings Characteristics

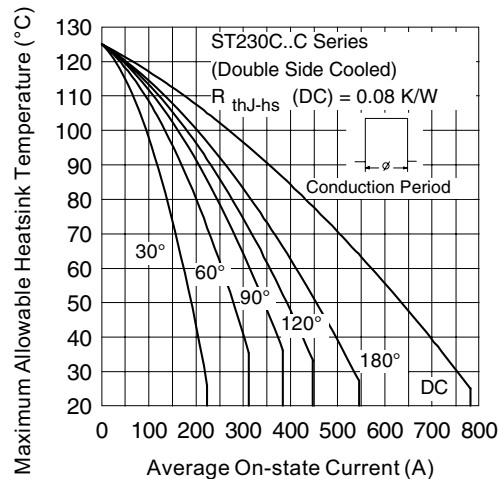


Fig. 4 - Current Ratings Characteristics

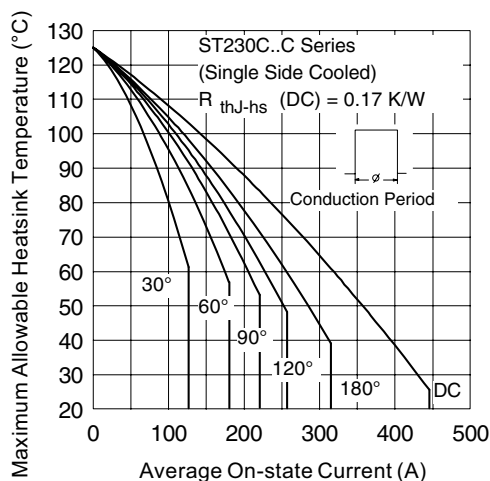


Fig. 2 - Current Ratings Characteristics

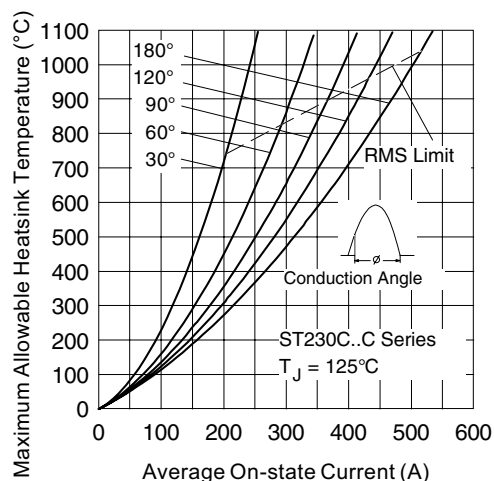


Fig. 5 - On-State Power Loss Characteristics

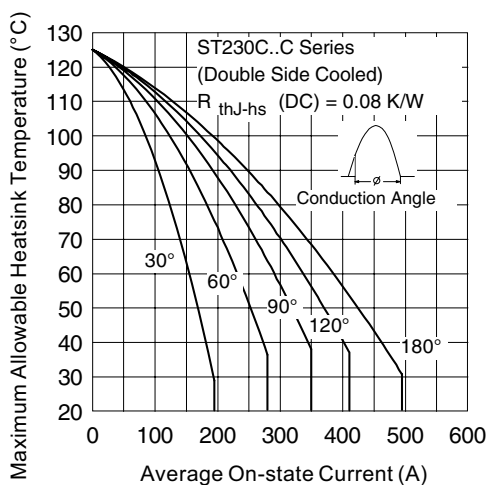


Fig. 3 - Current Ratings Characteristics

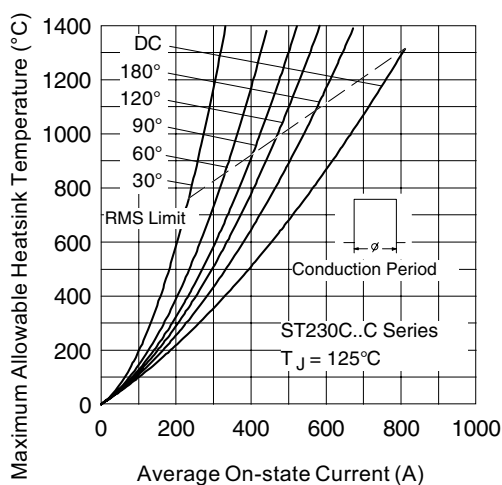


Fig. 6 - On-State Power Loss Characteristics

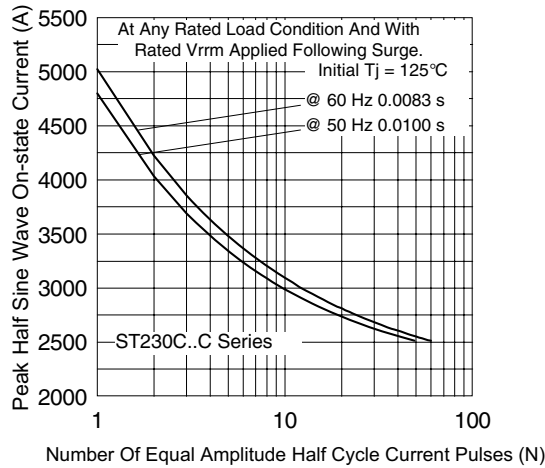


Fig. 7 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

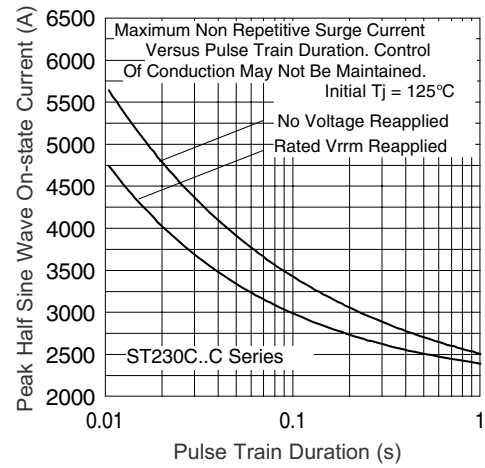


Fig. 8 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

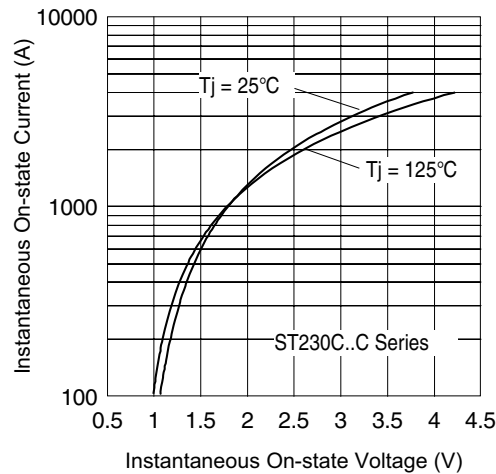


Fig. 9 - On-State Voltage Drop Characteristics

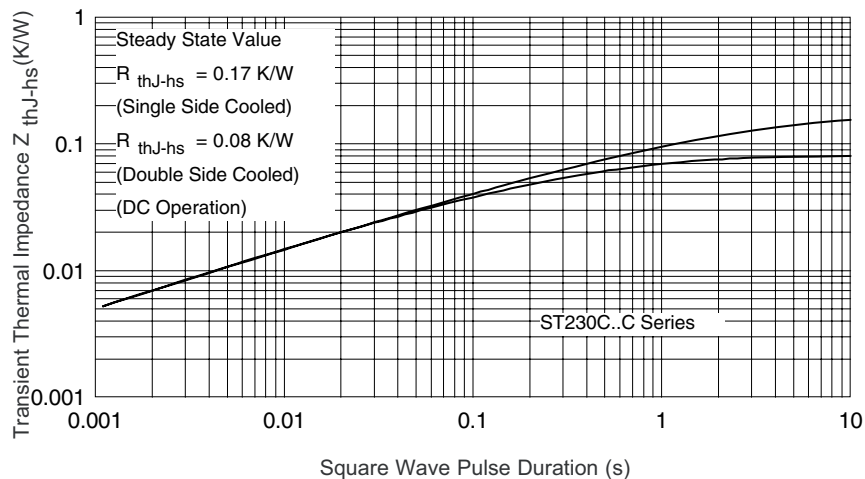


Fig. 10 - Thermal Impedance Z_{thJ-hs} Characteristics

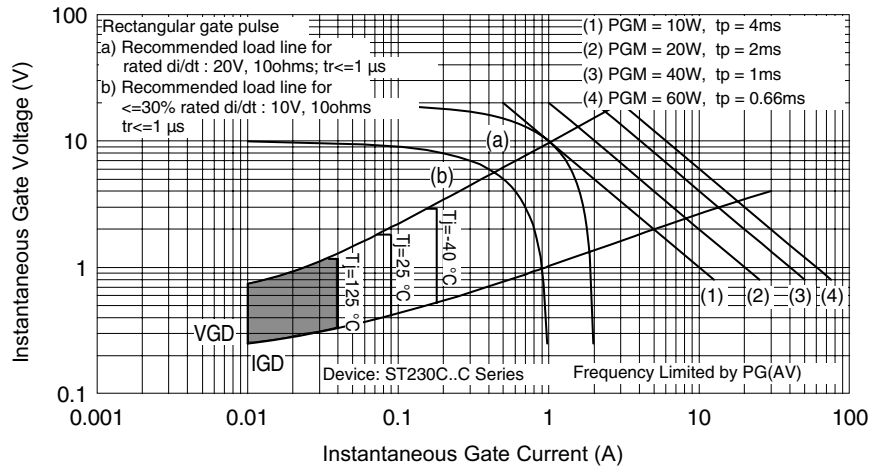


Fig. 11 - Gate Characteristics

ORDERING INFORMATION TABLE

Device code	ST	23	0	C	20	C	1		PbF
	①	②	③	④	⑤	⑥	⑦	⑧	⑨

- ① - Thyristor
- ② - Essential part number
- ③ - 0 = Converter grade
- ④ - C = Ceramic PUK
- ⑤ - Voltage code x 100 = V_{RRM} (see Voltage Ratings table)
- ⑥ - C = PUK case TO-200AB (A-PUK)
- ⑦ - 0 = Eyelet terminals (gate and auxiliary cathode unsoldered leads)
1 = Fast-on terminals (gate and auxiliary cathode unsoldered leads)
2 = Eyelet terminals (gate and auxiliary cathode soldered leads)
3 = Fast-on terminals (gate and auxiliary cathode soldered leads)
- ⑧ - Critical dV/dt : • None = 500 V/ μs (Standard selection)
• L = 1000 V/ μs (Special selection)
- ⑨ - Lead (Pb)-free

LINKS TO RELATED DOCUMENTS	
Dimensions	http://www.vishay.com/doc?95074



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